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#### DATASHEET

#### Description

The 9DBV0931 is a member of IDT's Full-Featured PCIe family. The device has 9 output enables for clock management, and 3 selectable SMBus addresses.

## **Recommended Application**

PCIe Gen1–3 clock distribution in Storage, Networking, Compute, Consumer

## **Output Features**

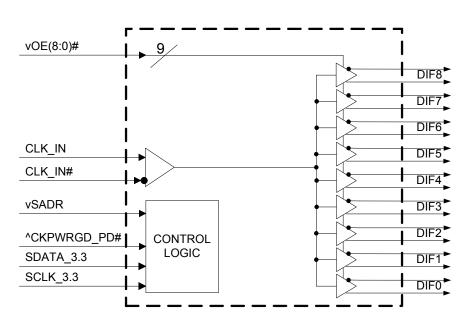
• 9 1–200MHz Low-Power (LP) HCSL DIF pairs

## **Key Specifications**

- Additive cycle-to-cycle jitter <5ps
- Output-to-output skew < 60ps</li>
- Additive phase jitter is < 100fs rms for PCIe Gen3
- Additive phase jitter < 300fs rms (12kHz-20MHz at125MHz)

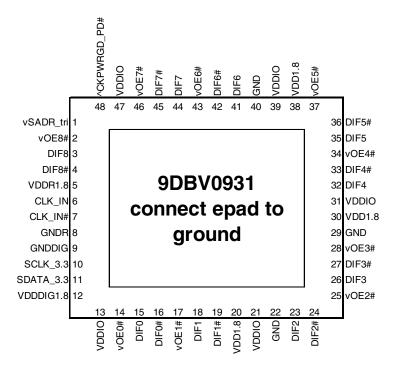
#### **Features/Benefits**

- LP-HCSL outputs; save 18 resistors and 31mm<sup>2</sup> compared to standard HCSL
- 53mW typical power consumption; eliminates thermal concerns
- Outputs can optionally be supplied from any voltage between 1.05V and 1.8V; maximum power savings
- OE# pins; support DIF power management
- HCSL-compatible differential input; can be driven by common clock sources
- SMBus-selectable features allow optimization to customer requirements
  - Slew rate for each output; allows tuning for various line lengths
  - Differential output amplitude; allows tuning for various application environments
- 1MHz to 200MHz operating frequency
- 3.3V tolerant SMBus interface works with legacy controllers
- Selectable SMBus addresses; multiple devices can easily share an SMBus segment
- Device contains default configuration; SMBus interface not required for device operation
- 6 x 6 mm 48-VFQFPN; minimal board space



## **Block Diagram**

## **Pin Configuration**



#### 48-pin VFQFPN, 6x6 mm, 0.4mm pitch

- ^v prefix indicates internal 120KOhm pull up AND pull down resistor (biased to VD
- v prefix indicates internal 120KOhm pull down resistor
- ^ prefix indicates internal 120KOhm pull up resistor

#### **SMBus Address Selection Table**

	SADR	Address	+ Read/Write bit
State of SADR on first application of	0	1101011	Х
CKPWRGD PD#	М	1101100	Х
	1	1101101	х

#### **Power Management Table**

CKPWRGD PD#	CLK_IN	SMBus	OEx# Pin	DIFx			
		OEx bit		True O/P	Comp. O/P		
0	Х	Х	Х	Low	Low		
1	Running	0	Х	Low	Low		
1	Running	1	0	Running	Running		
1	Running	1	1	Low	Low		

#### **Power Connections**

Pin Number			Description
VDD	VDDIO	GND	Description
			Input
5		8	receiver
			analog
12		9	Digital power
20,30,31,38	13,21,31,39, 47	22,29,40	DIF outputs

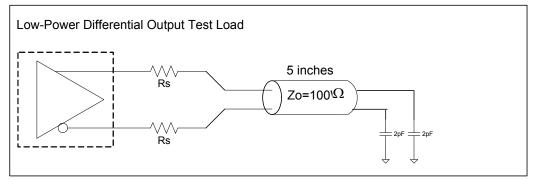
## **Pin Descriptions**

PIN #	PIN NAME	TYPE	DESCRIPTION
4		LATCHED	Tri-level latch to select SMBus Address. It has an internal 120kohm pull down
1	vSADR_tri	IN	resistor. See SMBus Address Selection Table.
			Active low input for enabling output 8. This pin has an internal 120kohm pull-
2	vOE8#	IN	down.
			1 = disable outputs, 0 = enable outputs.
3	DIF8	OUT	Differential true clock output.
4	DIF8#	OUT	Differential complementary clock output.
5	VDDR1.8	PWR	Power supply for differential input clock (receiver). This VDD should be treated as an analog power rail and filtered appropriately. Nominally 1.8V.
6	CLK_IN	IN	True input for differential reference clock.
7	CLK_IN#	IN	Complementary input for differential reference clock.
8	GNDR	GND	Analog ground pin for the differential input (receiver).
9	GNDDIG	GND	Ground pin for digital circuitry.
10	SCLK_3.3	IN	Clock pin of SMBus circuitry, 3.3V tolerant.
11	SDATA_3.3	I/O	Data pin for SMBus circuitry, 3.3V tolerant.
12	VDDDIG1.8	PWR	1.8V digital power (dirty power).
13	VDDIO	PWR	Power supply for differential outputs.
			Active low input for enabling output 0. This pin has an internal 120kohm pull-
14	vOE0#	IN	down.
			1 = disable outputs, $0 = $ enable outputs.
15	DIF0	OUT	Differential true clock output.
16	DIF0#	OUT	Differential complementary clock output.
			Active low input for enabling output 1. This pin has an internal 120kohm pull-
17	vOE1#	IN	down.
			1 = disable outputs, 0 = enable outputs.
18	DIF1	OUT	Differential true clock output.
19	DIF1#	OUT	Differential complementary clock output.
20	VDD1.8	PWR	Power supply, nominally 1.8V.
21	VDDIO	PWR	Power supply for differential outputs.
22	GND	GND	Ground pin.
23	DIF2	OUT	Differential true clock output.
24	DIF2#	OUT	Differential complementary clock output.
			Active low input for enabling output 2. This pin has an internal 120kohm pull-
25	vOE2#	IN	down.
			1 = disable outputs, 0 = enable outputs.
26	DIF3	OUT	Differential true clock output.
27	DIF3#	OUT	Differential complementary clock output.
			Active low input for enabling output 3. This pin has an internal 120kohm pull-
28	vOE3#	IN	down.
			1 = disable outputs, 0 = enable outputs.
29	GND	GND	Ground pin.
30	VDD1.8	PWR	Power supply, nominally 1.8V.
31	VDDIO	PWR	Power supply for differential outputs.
32	DIF4	OUT	Differential true clock output.
33	DIF4#	OUT	Differential complementary clock output.
			Active low input for enabling output 4. This pin has an internal 120kohm pull-
34	vOE4#	IN	down.
			1 = disable outputs, 0 = enable outputs.

## Pin Descriptions (cont.)

PIN #	PIN NAME	TYPE	DESCRIPTION
35	DIF5	OUT	Differential true clock output.
36	DIF5#	OUT	Differential complementary clock output.
37	vOE5#	IN	Active low input for enabling output 5. This pin has an internal 120kohm pull- down. 1 = disable outputs, 0 = enable outputs.
38	VDD1.8	PWR	Power supply, nominally 1.8V.
39	VDDIO	PWR	Power supply for differential outputs.
40	GND	GND	Ground pin.
41	DIF6	OUT	Differential true clock output.
42	DIF6#	OUT	Differential complementary clock output.
43	vOE6#	IN	Active low input for enabling output 6. This pin has an internal 120kohm pull- down. 1 = disable outputs, 0 = enable outputs.
44	DIF7	OUT	Differential true clock output.
45	DIF7#	OUT	Differential complementary clock output.
46	vOE7#	IN	Active low input for enabling output 7. This pin has an internal 120kohm pull- down. 1 = disable outputs, 0 = enable outputs.
47	VDDIO	PWR	Power supply for differential outputs.
48	^CKPWRGD_PD#	IN	Input notifies device to sample latched inputs and start up on first high assertion. Low enters Power Down Mode, subsequent high assertions exit Power Down Mode. This pin has internal 120kohm pull-up resistor.
49	EPAD	GND	Connect epad to ground.

## **Test Loads**



#### **Alternate Differential Output Terminations**

Rs	Zo	Units
33	100	Ohms
27	85	Onins

#### **Alternate Terminations**

The 9DBV0931 can easily drive LVPECL, LVDS, and CML logic. See <u>"AN-891 Driving LVPECL, LVDS, and CML Logic with IDT's</u> <u>"Universal" Low-Power HCSL Outputs</u>" for details.

## **Absolute Maximum Ratings**

Stresses above the ratings listed below can cause permanent damage to the 9DBV0931. These ratings, which are standard values for IDT commercially rated parts, are stress ratings only. Functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods can affect product reliability. Electrical parameters are guaranteed only over the recommended operating temperature range.

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Supply Voltage	V <sub>DD</sub> x	Applies to $V_{DD}$ , $V_{DDA}$ and $V_{DDIO}$	-0.5		2.5	V	1,2
Input Voltage	V <sub>IN</sub>		-0.5		V <sub>DD</sub> +0.5	V	1,3
Input High Voltage, SMBus	VIHSMB	SMBus clock and data pins			3.3	V	1
Storage Temperature	Ts		-65		150	°C	1
Junction Temperature	Tj				125	°C	1
Input ESD Protection	ESD prot	Human Body Model	2000			V	1

<sup>1</sup> Guaranteed by design and characterization, not 100% tested in production.

<sup>2</sup> Operation under these conditions is neither implied nor guaranteed.

<sup>3</sup> Not to exceed 2.5V.

#### **Electrical Characteristics–Clock Input Parameters**

 $TA = T_{COM}$  or  $T_{IND}$ ; Supply voltages per normal operation conditions; see Test Loads for loading conditions

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Input Crossover Voltage - DIF_IN	V <sub>CROSS</sub>	Cross over voltage	150		900	mV	1
Input Swing - DIF_IN	V <sub>SWING</sub>	Differential value	300			mV	1
Input Slew Rate - DIF_IN	dv/dt	Measured differentially	0.4		8	V/ns	1,2
Input Leakage Current	I <sub>IN</sub>	$V_{IN} = V_{DD}$ , $V_{IN} = GND$	-5		5	μA	
Input Duty Cycle	d <sub>tin</sub>	Measurement from differential waveform	40		60	%	1
Input Jitter - Cycle to Cycle	$J_{DIFIn}$	Differential measurement	0		125	ps	1

<sup>1</sup> Guaranteed by design and characterization, not 100% tested in production.

<sup>2</sup> Slew rate measured through +/-75mV window centered around differential zero.

# Electrical Characteristics–Input/Supply/Common Parameters–Normal Operating Conditions

TA = T<sub>COM</sub> or T<sub>IND</sub>; Supply voltages per normal operation conditions; see Test Loads for loading conditions

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	МАХ	UNITS	NOTES
Supply Voltage	VDDx	Supply voltage for core and analog	1.7	1.8	1.9	V	
Output Supply Voltage	VDDIO	Low Voltage Supply LP-HCSL Outputs	0.9975	1.05-1.8	1.9	V	
Ambient Operating	T <sub>COM</sub>	Commercial range	0	25	70	°C	1
Temperature	T <sub>IND</sub>	Industrial range	-40	25	85	°C	1
Input High Voltage	V <sub>IH</sub>	Single-ended inputs, except SMBus	0.75 V <sub>DD</sub>		$V_{DD} + 0.3$	V	
Input Mid Voltage	VIM	Single-ended tri-level inputs ('_tri' suffix)	0.4 V <sub>DD</sub>		0.6 V <sub>DD</sub>	V	
Input Low Voltage	V <sub>IL</sub>	Single-ended inputs, except SMBus	-0.3		0.25 V <sub>DD</sub>	V	
	I <sub>IN</sub>	Single-ended inputs, $V_{IN} = GND$ , $V_{IN} = V_{DD}$	-5		5	μA	
Input Current		Single-ended inputs					
Input Current	I <sub>INP</sub>	V <sub>IN</sub> = 0 V; Inputs with internal pull-up resistors	-200		200	μA	
		$V_{IN} = V_{DD}$ ; Inputs with internal pull-down resistors					
Input Frequency	F <sub>in</sub>		1		200	MHz	2
Pin Inductance	L <sub>pin</sub>				7	nH	1
	CIN	Logic Inputs, except DIF_IN	1.5		5	pF	1
Capacitance	$C_{INDIF_IN}$	DIF_IN differential clock inputs	1.5		2.7	pF	1,6
	COUT	Output pin capacitance			6	pF	1
Clk Stabilization	T <sub>STAB</sub>	From V <sub>DD</sub> power-up and after input clock stabilization or de-assertion of PD# to 1st clock			1	ms	1,2
Input SS Modulation Frequency PCIe	f <sub>MODINPCIe</sub>	Allowable frequency for PCIe applications (Triangular modulation)	30		33	kHz	
Input SS Modulation Frequency non-PCIe	f <sub>MODIN</sub>	Allowable frequency for non-PCIe applications (Triangular modulation)	0		66	kHz	
OE# Latency	t <sub>LATOE#</sub>	DIF start after OE# assertion DIF stop after OE# deassertion	1		3	clocks	1,3
Tdrive_PD#	t <sub>DRVPD</sub>	DIF output enable after PD# de-assertion			300	μs	1,3
Tfall	t <sub>F</sub>	Fall time of single-ended control inputs			5	ns	2
Trise	t <sub>R</sub>	Rise time of single-ended control inputs			5	ns	2
SMBus Input Low Voltage	VILSMB	$V_{DDSMB}$ = 3.3V, see note 4 for $V_{DDSMB}$ < 3.3V			0.8	V	4
SMBus Input High Voltage	VIHSMB	$V_{DDSMB}$ = 3.3V, see note 5 for $V_{DDSMB}$ < 3.3V	2.1		3.3	V	5
SMBus Output Low Voltage	V <sub>OLSMB</sub>	at I <sub>PULLUP</sub>			0.4	V	
SMBus Sink Current	I <sub>PULLUP</sub>	at V <sub>OL</sub>	4			mA	
Nominal Bus Voltage	V <sub>DDSMB</sub>	Bus voltage	1.7		3.6	V	
SCLK/SDATA Rise Time	t <sub>RSMB</sub>	(Max V <sub>IL</sub> - 0.15V) to (Min V <sub>IH</sub> + 0.15V)			1000	ns	1
SCLK/SDATA Fall Time	t <sub>FSMB</sub>	(Min V <sub>IH</sub> + 0.15V) to (Max V <sub>IL</sub> - 0.15V)			300	ns	1
SMBus Operating Frequency	f <sub>MAXSMB</sub>	Maximum SMBus operating frequency			400	kHz	7

<sup>1</sup> Guaranteed by design and characterization, not 100% tested in production.

<sup>2</sup> Control input must be monotonic from 20% to 80% of input swing.

 $^{3}$  Time from deassertion until outputs are > 200 mV.

 $^4$  For V\_{DDSMB} < 3.3V, V\_{ILSMB} < = 0.35V\_{DDSMB.}

 $^5$  For V\_{DDSMB} < 3.3V, V\_{IHSMB} > = 0.65V\_{DDSMB.}

<sup>6</sup> DIF\_IN input.

<sup>7</sup> The differential input clock must be running for the SMBus to be active.

## **Electrical Characteristics–DIF Low-Power HCSL Outputs**

TA = T<sub>COM</sub> or T<sub>IND</sub>; Supply voltages per normal operation conditions; see Test Loads for loading conditions

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Clow Data	Trf	Scope averaging on, fast slew rate setting	2.3	3.4	4.3	V/ns	1,2,3
Slew Rate	In	Scope averaging on, slow slew rate setting	1.4	2.2	3.1	V/ns	1,2,3
Slew Rate Matching	∆Trf	Slew rate matching, scope averaging on		5	20	%	1,2,4
Voltage High	V <sub>HIGH</sub>	Statistical measurement on single-ended signal	660	774	850	m)/	7
Voltage Low	V <sub>LOW</sub>	using oscilloscope math function.		0	150	mV	7
Max Voltage	Vmax	Measurement on single ended signal using		813	1150	mV	7
Min Voltage	Vmin	absolute value. (Scope averaging off)	-300	-55		mv	7
Vswing	Vswing	Scope averaging off	300	1548		mV	1,2
Crossing Voltage (abs)	Vcross_abs	Scope averaging off	250	404	550	mV	1,5
Crossing Voltage (var)	∆-Vcross	Scope averaging off		12	140	mV	1,6

<sup>1</sup>Guaranteed by design and characterization, not 100% tested in production.  $C_L = 2pF$  with  $R_S = 33\Omega$  for  $Zo = 50\Omega$  (100 $\Omega$  differential trace impedance).

<sup>2</sup> Measured from differential waveform.

<sup>3</sup> Slew rate is measured through the Vswing voltage range centered around differential 0V. This results in a +/-150mV window around differential 0V.

<sup>4</sup> Matching applies to rising edge rate for Clock and falling edge rate for Clock#. It is measured using a +/-75mV window centered on the average cross point where Clock rising meets Clock# falling. The median cross point is used to calculate the voltage thresholds the oscilloscope is to use for the edge rate calculations.

<sup>5</sup> Vcross is defined as voltage where Clock = Clock# measured on a component test board and only applies to the differential rising edge (i.e. Clock rising and Clock# falling).

<sup>6</sup> The total variation of all Vcross measurements in any particular system. Note that this is a subset of Vcross\_min/max (Vcross absolute) allowed. The intent is to limit Vcross induced modulation by setting  $\Delta$ -Vcross to be smaller than Vcross absolute.

<sup>7</sup> 660mV Vhigh is the minimum when VDDIO is > = 1.05V + -5%. If VDDIO is < 1.05V + -5%, the minimum Vhigh will be VDDIOmin - 250mV. For example, for VDDIO = 0.9V + -5%, VHIGHmin will be 860mV - 250mV = 610mV.

## **Electrical Characteristics–Current Consumption**

 $TA = T_{COM}$  or  $T_{IND}$ ; Supply voltages per normal operation conditions; see Test Loads for loading conditions

			5				
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Operating Supply Current	I <sub>DDR</sub>	VDDR at 100MHz		2.5	5	mA	1
	I <sub>DDDIG</sub>	VDDIG, all outputs at 100MHz		5.7	8	mA	1
	I <sub>DDO</sub>	VDDO1.8 + VDDIO, all outputs at 100MHz		36	45	mA	1
	I <sub>DDRPD</sub>	VDDR, CKPWRGD_PD# = 0		0.4	1	mA	1, 2
Powerdown Current	IDDDIGPD	VDDDIG, CKPWRGD_PD# = 0		0.6	1.5	mA	1, 2
Image: Description of the second state of the sec	0.1	mA	1, 2				

<sup>1</sup> Guaranteed by design and characterization, not 100% tested in production.

<sup>2</sup> Input clock stopped.

## Electrical Characteristics–Output Duty Cycle, Jitter, Skew and PLL Characteristics

 $TA = T_{COM}$  or  $T_{IND}$ ; Supply voltages per normal operation conditions; see Test Loads for loading conditions

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Duty Cycle Distortion	t <sub>DCD</sub>	Measured differentially at 100MHz	-1	-0.4	0.5	%	1,3
Skew, Input to Output	t <sub>pdBYP</sub>	V <sub>T</sub> = 50%	1800	2378	3000	ps	1
Skew, Output to Output	t <sub>sk3</sub>	V <sub>T</sub> = 50%		41	60	ps	1,4
Jitter, Cycle to Cycle	t <sub>jcyc-cyc</sub>	Additive Jitter		0.1	5	ps	1,2

<sup>1</sup> Guaranteed by design and characterization, not 100% tested in production.

<sup>2</sup> Measured from differential waveform.

<sup>3</sup> Duty cycle distortion is the difference in duty cycle between the output and the input clock.

<sup>4</sup> All outputs at default slew rate.

#### **Electrical Characteristics–Phase Jitter Parameters**

TA = T<sub>COM</sub> or T<sub>IND</sub>; Supply voltages per normal operation conditions; see Test Loads for loading conditions

						INDUSTRY		
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	LIMIT	UNITS	Notes
	t <sub>jphPCleG1</sub>	PCIe Gen 1		0.1	5	N/A	ps (p-p)	1,2,3,5
	+	PCIe Gen 2 Lo Band 10kHz < f < 1.5MHz		0.1	0.4	N/A	ps (rms)	1,2,3,4,5
	t <sub>jphPCle</sub> G2	PCIe Gen 2 High Band 1.5MHz < f < Nyquist (50MHz)		0.01	0.4	N/A	ps (rms)	1,2,3,4
Additive Phase Jitter	t <sub>jphPCleG3</sub>	PCIe Gen 3 (2-4MHz or 2-5MHz, CDR = 10MHz)		0.00	0.1	N/A	ps (rms)	1,2,3,4
	t <sub>jphSGMIIM0</sub>	125MHz, 1.5MHz to 10MHz, -20dB/decade rollover < 1.5MHz, -40db/decade rolloff > 10MHz		165	200	N/A	fs (rms)	1,6
	t <sub>jphSGMIIM1</sub>	125MHz, 12kHz to 20MHz, -20dB/decade rollover < 1.5MHz, -40db/decade rolloff > 10MHz		251	300	N/A	fs (rms)	1,6

<sup>1</sup> Guaranteed by design and characterization, not 100% tested in production.

<sup>2</sup> See http://www.pcisig.com for complete specs.

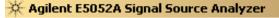
<sup>3</sup> Sample size of at least 100K cycles. This figure extrapolates to 108ps pk-pk at 1M cycles for a BER of 1-12.

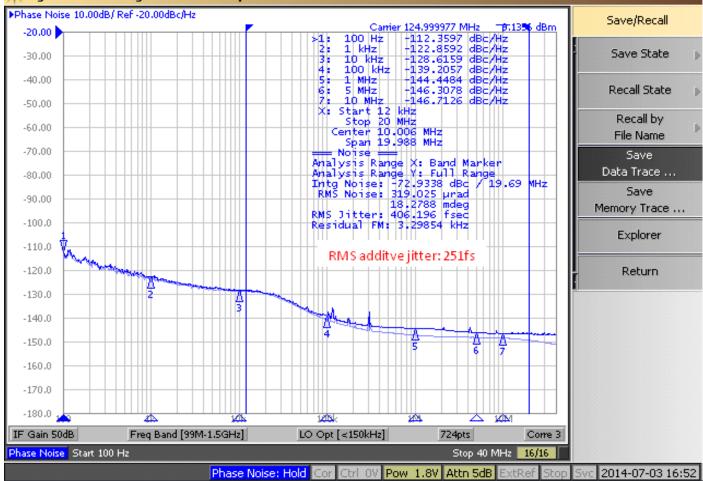
<sup>4</sup> For RMS figures, additive jitter is calculated by solving the following equation: Additive jitter = SQRT[(total jitter)<sup>2</sup> - (input jitter)<sup>2</sup>].

<sup>5</sup> Driven by 9FGV0831 or equivalent.

<sup>6</sup> Rohde & Schwarz SMA100.

## Additive Phase Jitter Plot: 125M (12kHz to 20MHz)





#### How to Write

DT

- Controller (host) sends a start bit
- Controller (host) sends the write address
- IDT clock will acknowledge
- Controller (host) sends the beginning byte location = N
- IDT clock will acknowledge
- Controller (host) sends the byte count = X
- IDT clock will **acknowledge**
- Controller (host) starts sending Byte N through Byte N+X-1
- IDT clock will acknowledge each byte one at a time
- Controller (host) sends a stop bit

	Index Bl	ock \	Write Operation
Controll	er (Host)		IDT (Slave/Receiver)
Т	starT bit		
Slave A	Address		
WR	WRite		
			ACK
Beginning	g Byte = N		
			ACK
Data Byte	Count = X		
			ACK
Beginnin	ig Byte N		
			ACK
0		×	
0		X Byte	0
0		Φ	0
			0
Byte N	+ X - 1		
			ACK
Р	stoP bit		

Note: SMBus Address is Latched on SADR pin.

#### How to Read

- Controller (host) will send a start bit
- Controller (host) sends the write address
- IDT clock will acknowledge
- Controller (host) sends the beginning byte location = N
- IDT clock will acknowledge
- Controller (host) will send a separate start bit
- Controller (host) sends the read address
- IDT clock will acknowledge
- IDT clock will send the data byte count = X
- IDT clock sends Byte N+X-1
- IDT clock sends Byte 0 through Byte X (if X<sub>(H)</sub> was written to Byte 8)
- Controller (host) will need to acknowledge each byte
- Controller (host) will send a not acknowledge bit
- Controller (host) will send a stop bit

	Index Block F	Read O	peration
Cor	ntroller (Host)		IDT (Slave/Receiver)
Т	starT bit		
SI	ave Address	_	
WR	WR WRite		
			ACK
Begi	nning Byte = N		
			ACK
RT	Repeat starT		
SI	ave Address		
RD	RD ReaD		
			ACK
			Data Byte Count=X
	ACK		
		_	Beginning Byte N
	ACK		
		e	0
	0	X Byte	0
	0		0
0			
			Byte N + X - 1
N	Not acknowledge		
Р	stoP bit		

#### **Control Function** Default Byte 0 Name Туре 0 1 OE# pin control Bit 7 DIF OE7 Output Enable RW Low/Low 1 DIF OE6 Output Enable RW Low/Low OE# pin control 1 Bit 6 Bit 5 DIF OE5 Output Enable RW Low/Low OE# pin control 1 Output Enable RW OE# pin control 1 Bit 4 DIF OE4 Low/Low DIF OE3 Output Enable RW OE# pin control Bit 3 Low/Low 1 Bit 2 DIF OE2 Output Enable RW Low/Low OE# pin control 1 Output Enable RW OE# pin control Bit 1 DIF OE1 Low/Low 1 Bit 0 DIF OE0 **Output Enable** RW Low/Low OE# pin control 1

#### SMBus Table: Output Enable Register <sup>1</sup>

1. A low on these bits will override the OE# pin and force the differential output Low/Low

#### SMBus Table: Output Enable and Output Amplitude Control Register

Byte 1	Name	Control Function	Туре	0	1	Default
Bit 7		Reserved				0
Bit 6		Reserved				1
Bit 5	DIF OE8 Output Enable RW Low/Low OE# pin control					1
Bit 4		Reserved				0
Bit 3		Reserved				1
Bit 2		Reserved				1
Bit 1	AMPLITUDE 1	Controls Output Amplitude	Controls Output Amplitude RW 00 = 0.6V 01 = 0.7V			
Bit 0	AMPLITUDE 0		RW	10= 0.8V	11 = 0.9V	0

1. A low on the DIF OE bit will override the OE# pin and force the differential output Low/Low

#### SMBus Table: DIF Slew Rate Control Register

Byte 2	Name	Control Function	Туре	0	1	Default
Bit 7 SLEWRATESEL DIF7		Adjust Slew Rate of DIF7	RW	Slow setting	Fast setting	1
Bit 6	SLEWRATESEL DIF6	Adjust Slew Rate of DIF6	RW	Slow setting	Fast setting	1
Bit 5	SLEWRATESEL DIF5	Adjust Slew Rate of DIF5	RW	Slow setting	Fast setting	1
Bit 4	SLEWRATESEL DIF4	Adjust Slew Rate of DIF4	RW	Slow setting	Fast setting	1
Bit 3	SLEWRATESEL DIF3	Adjust Slew Rate of DIF3	RW	Slow setting	Fast setting	1
Bit 2	SLEWRATESEL DIF2	Adjust Slew Rate of DIF2	RW	Slow setting	Fast setting	1
Bit 1 SLEWRATESEL DIF1		Adjust Slew Rate of DIF1	RW	Slow setting	Fast setting	1
Bit 0 SLEWRATESEL DIF0		Adjust Slew Rate of DIF0	RW	Slow setting	Fast setting	1

#### SMBus Table: DIF Slew Rate Control Register

Byte 3	Name	Control Function	Туре	0	1	Default
Bit 7		Reserved				1
Bit 6		Reserved				1
Bit 5		Reserved				0
Bit 4		Reserved				0
Bit 3		Reserved				0
Bit 2		Reserved				1
Bit 1	Reserved					
Bit 0	SLEWRATESEL DIF8 Adjust Slew Rate of DIF8 RW Slow setting Fast setting				1	

#### Byte 4 is Reserved and reads back 'hFF

#### SMBus Table: Revision and Vendor ID Register

Byte 5	Name	Control Function	Туре	0	1	Default
Bit 7	RID3		R		0	
Bit 6	RID2	Revision ID R A rev = 0000	0			
Bit 5	RID1		0			
Bit 4	RID0		R		0	
Bit 3	VID3		R			0
Bit 2	VID2	VENDOR ID	R	0001		0
Bit 1	VID1		0			
Bit 0	VID0		R	1		

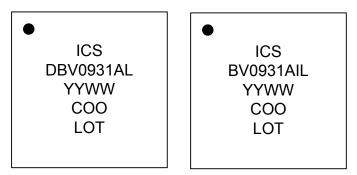
#### SMBus Table: Device Type/Device ID

Byte 6	Name	Control Function	Туре	0	1	Default
Bit 7	Device Type1	Device Type	R	00 = FG,	01 = DB	1
Bit 6	Device Type0	Device Type	R	10 = DM, 11=	DB fanout only	1
Bit 5	Device ID5		R			0
Bit 4	Device ID4	1	R			0
Bit 3	Device ID3	Device ID	R	001001 bina	n or 00 hox	1
Bit 2	Device ID2	Device ID	R	001001 011a		0
Bit 1	Device ID1	R			0	
Bit 0	Device ID0	7	R			1

#### SMBus Table: Byte Count Register

Byte 7	Name	Control Function	Туре	0	1	Default
Bit 7		Reserved				0
Bit 6		Reserved				0
Bit 5		Reserved				0
Bit 4	BC4		RW			0
Bit 3	BC3		RW	Writing to this regist	er will configure how	1
Bit 2	BC2	Byte Count Programming	RW	many bytes will be r	ead back, default is	0
Bit 1	BC1		RW	= 8 b	ytes.	0
Bit 0	BC0		RW			0

#### **Marking Diagrams**



Notes:

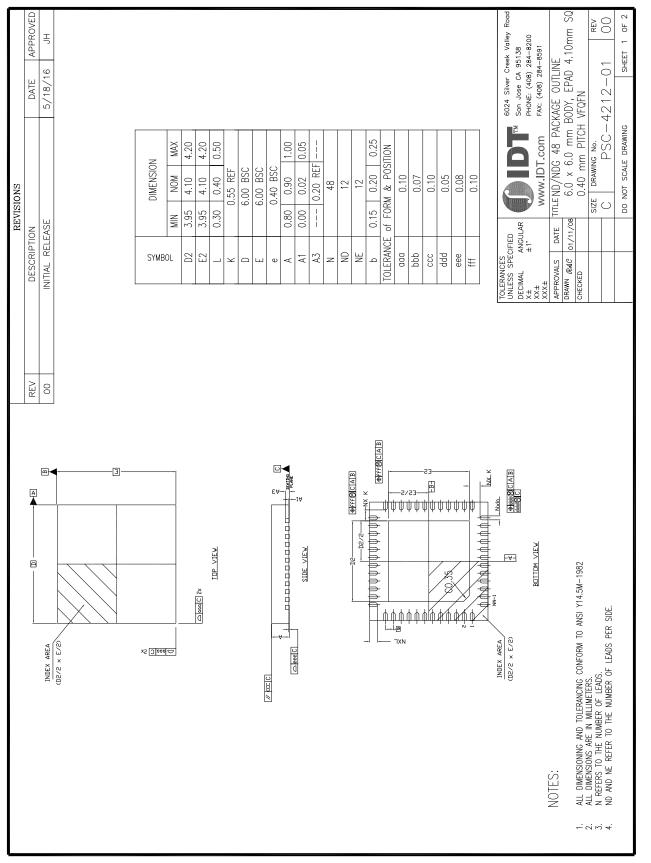
- 1. "LOT" is the lot sequence number.
- 2. "COO" denotes country of origin.
- 3. YYWW is the last two digits of the year and week that the part was assembled.
- 4. Line 2: truncated part number.
- 5. "L" denotes RoHS compliant package.
- 6. "I" denotes industrial temperature range device.

#### **Thermal Characteristics**

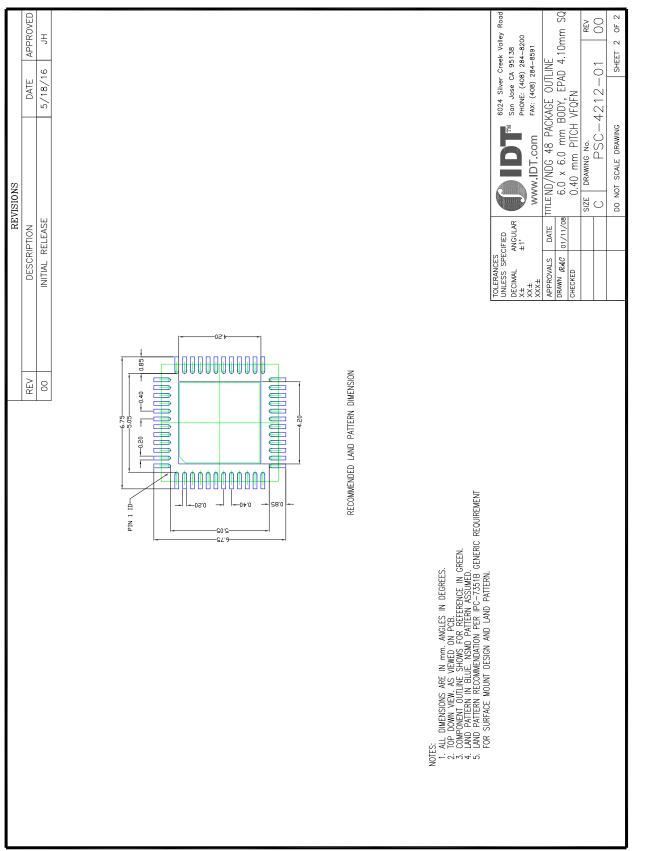
PARAMETER	SYMBOL	CONDITIONS	PKG	TYP VALUE	UNITS	NOTES
	θ <sub>JC</sub>	Junction to Case		33	°C/W	1
	$\theta_{Jb}$	Junction to Base		2.1	°C/W	1
Thermal Resistance	$\theta_{JA0}$	Junction to Air, still air	NDG48	37	°C/W	1
mermai nesistance	$\theta_{JA1}$	Junction to Air, 1 m/s air flow	NDG40	30	°C/W	1
	$\theta_{JA3}$	Junction to Air, 3 m/s air flow		27	°C/W	1
	$\theta_{JA5}$	Junction to Air, 5 m/s air flow		26	°C/W	1

<sup>1</sup>ePad soldered to board

## Package Outline and Dimensions (NDG48)



## Package Outline and Dimensions (NDG48), cont.



## **Ordering Information**

Part / Order Number	Shipping Packaging	Package	Temperature
9DBV0931AKLF	Trays	48-pin VFQFPN	0 to +70° C
9DBV0931AKLFT	Tape and Reel	48-pin VFQFPN	0 to +70° C
9DBV0931AKILF	Trays	48-pin VFQFPN	-40 to +85° C
9DBV0931AKILFT	Tape and Reel	48-pin VFQFPN	-40 to +85° C

"LF" suffix to the part number are the Pb-Free configuration and are RoHS compliant. "A" is the device revision designator (will not correlate with the datasheet revision).

## **Revision History**

Rev.	Initiator	Issue Date	Description	Page #
A	RDW	7/28/2014	<ol> <li>Updated front page text</li> <li>Updated block diagram</li> <li>Updated electrical tables</li> <li>Updated test loads diagrams.</li> <li>Updated Smbus byte 2, 3 and 6 labeling. Functionality did not change.</li> <li>Move to final.</li> </ol>	Various
В	RDW	8/27/2014	<ol> <li>Updated min Vhigh on DIF outputs from 630mV to 660mV, correcting a typo.</li> <li>Corrected Conditions for Slew Rate in DIF Low-Power HCSL Outputs</li> <li>Lowered maximum PCIe Gen3 additive phase jitter from 0.3ps rms to 0.1ps rms.</li> </ol>	8
с	RDW	8/28/2014	<ol> <li>Corrected Supply Voltage in Absolute Maximum Ratings.</li> <li>Lowered additive phase jitter specs.</li> </ol>	Various
D	RDW	3/25/2016	<ol> <li>Revised front page text extensively.</li> <li>Added note about Spread Spectrum Compatibility to the features.</li> <li>Change pin name of VDDA1.8 to VDD1.8 and GNDA to GND to clarify that this part does not have a PLL. This is a document change only. There is no silicon change.</li> <li>Corrected OE8# to indicate an internal pull down, not a pull up.</li> <li>Added epad nomenclature to DS</li> <li>Updated package drawing to latest version - no package change.</li> <li>Added reference to AN-891.</li> <li>Updated "Current Consumption" table to remove references to VDDA1.8</li> <li>Added "RMS additive phase jitter: 251fs" to phase noise plot</li> <li>Updated "Clock Input Parameters" table for consistency - no silicon change.</li> <li>Updated "Output Duty Cycle, Jitter, Skew and PLL Characteristics" and "Phase Jitter" tables to remove references to bypass mode.</li> </ol>	1-5,7-9 14
E	RDW	3/14/2017	<ol> <li>Removed "bypass mode." reference in note 3 under Output Duty Cycle table.</li> <li>Corrected spelling errors/typos.</li> <li>Change VDDA to VDDO1.8 in Current Consumption table.</li> <li>Update Additive Phase Jitter conditions for PCIe Gen3.</li> <li>Updated package outline drawings.</li> </ol>	8,9,15,16



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